

CBR1F-D020S SERIES

**SURFACE MOUNT
1 AMP FAST RECOVERY
SILICON BRIDGE RECTIFIER**

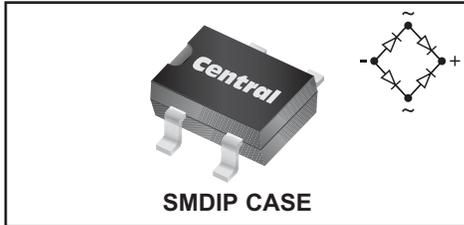


www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBR1F-D020S Series types are fast recovery, full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

MARKING: FULL PART NUMBER



MAXIMUM RATINGS:

($T_A=25^\circ\text{C}$ unless otherwise specified)

	SYMBOL	CBR1F-D020S	CBR1F-D040S	CBR1F-D060S	CBR1F-D080S	CBR1F-D100S	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V_R	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	140	280	420	560	700	V
Average Forward Current ($T_A=40^\circ\text{C}$)	I_O			1.0			A
Peak Forward Surge Current	I_{FSM}			50			A
Rating for Fusing ($t<8.35\text{ms}$)	I^2t			3.74			A ² s
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 to +150			$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_R	V_R =Rated V_{RRM}		5.0	μA
I_R	V_R =Rated V_{RRM} , $T_A=125^\circ\text{C}$		0.5	mA
V_F	$I_F=1.0\text{A}$		1.3	V
t_{rr}	$I_F=0.5\text{A}$, $I_R=1.0\text{A}$, Rec. to 0.25A (200V, 300V, 400V)		200	ns
t_{rr}	$I_F=0.5\text{A}$, $I_R=1.0\text{A}$, Rec. to 0.25A (600V)		300	ns
t_{rr}	$I_F=0.5\text{A}$, $I_R=1.0\text{A}$, Rec. to 0.25A (800V, 1000V)		500	ns
C_J	$V_R=4.0\text{V}$, $f=1.0\text{MHz}$	25		pF

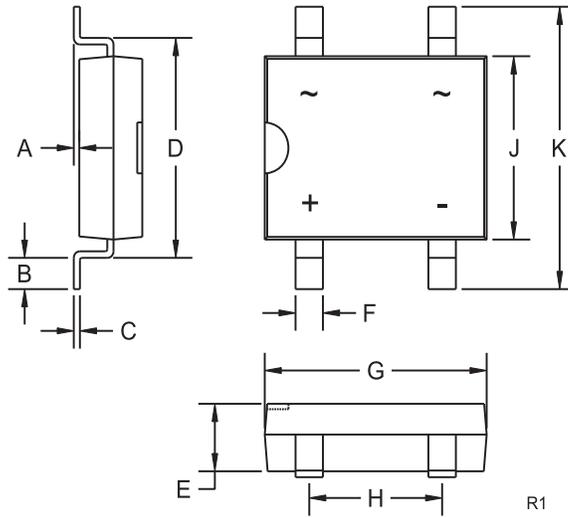
R1 (4-January 2010)

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SMDIP CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

MARKING: FULL PART NUMBER

R1 (4-January 2010)